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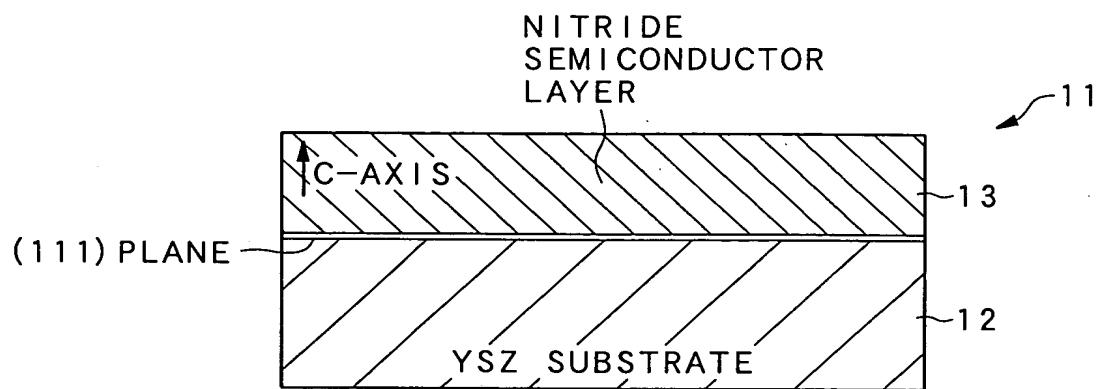


FIG. 1

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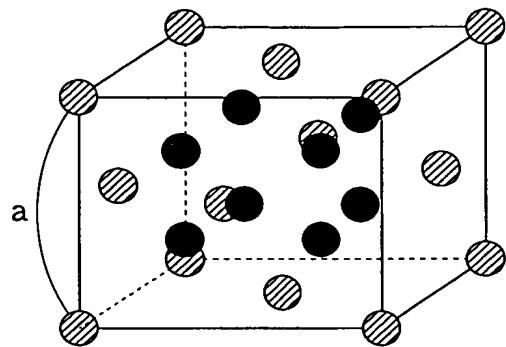


FIG. 2A

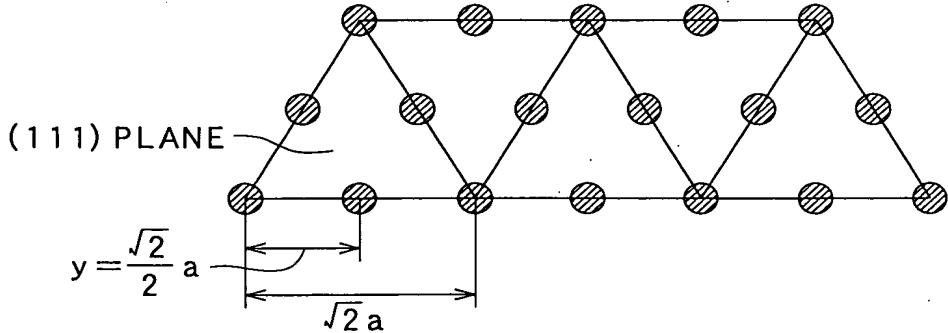


FIG. 2B

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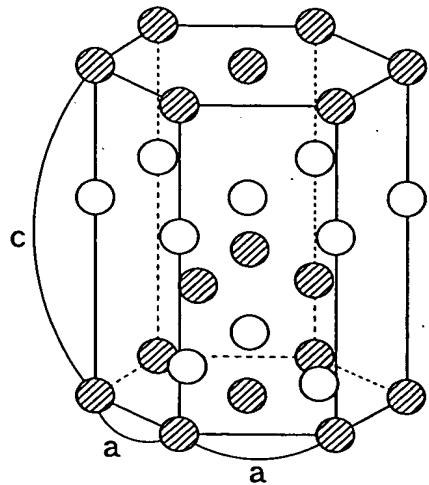


FIG. 3 A

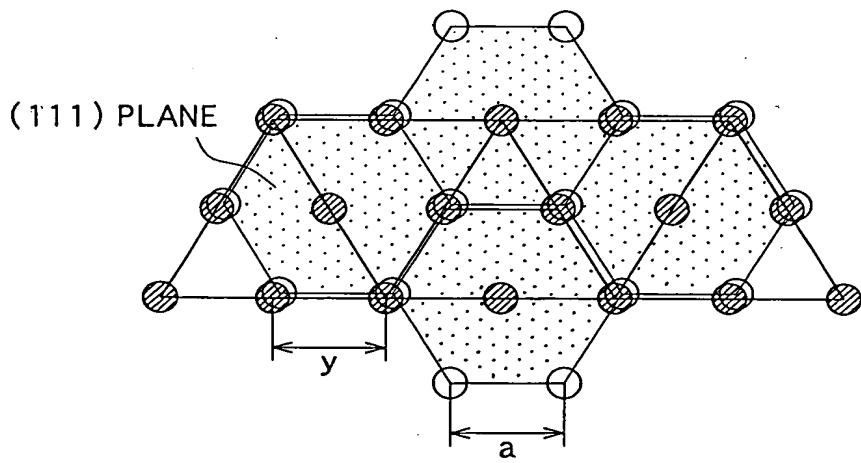


FIG. 3 B

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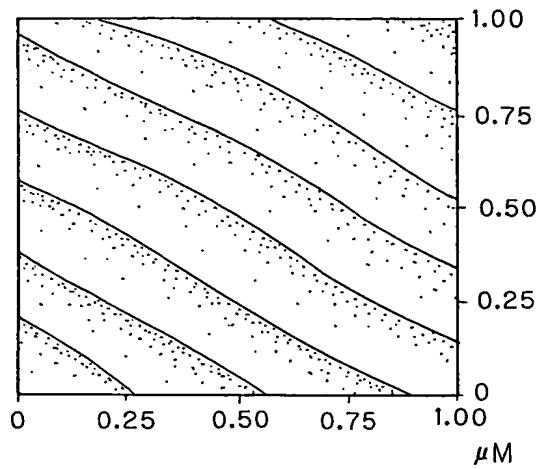


FIG. 4

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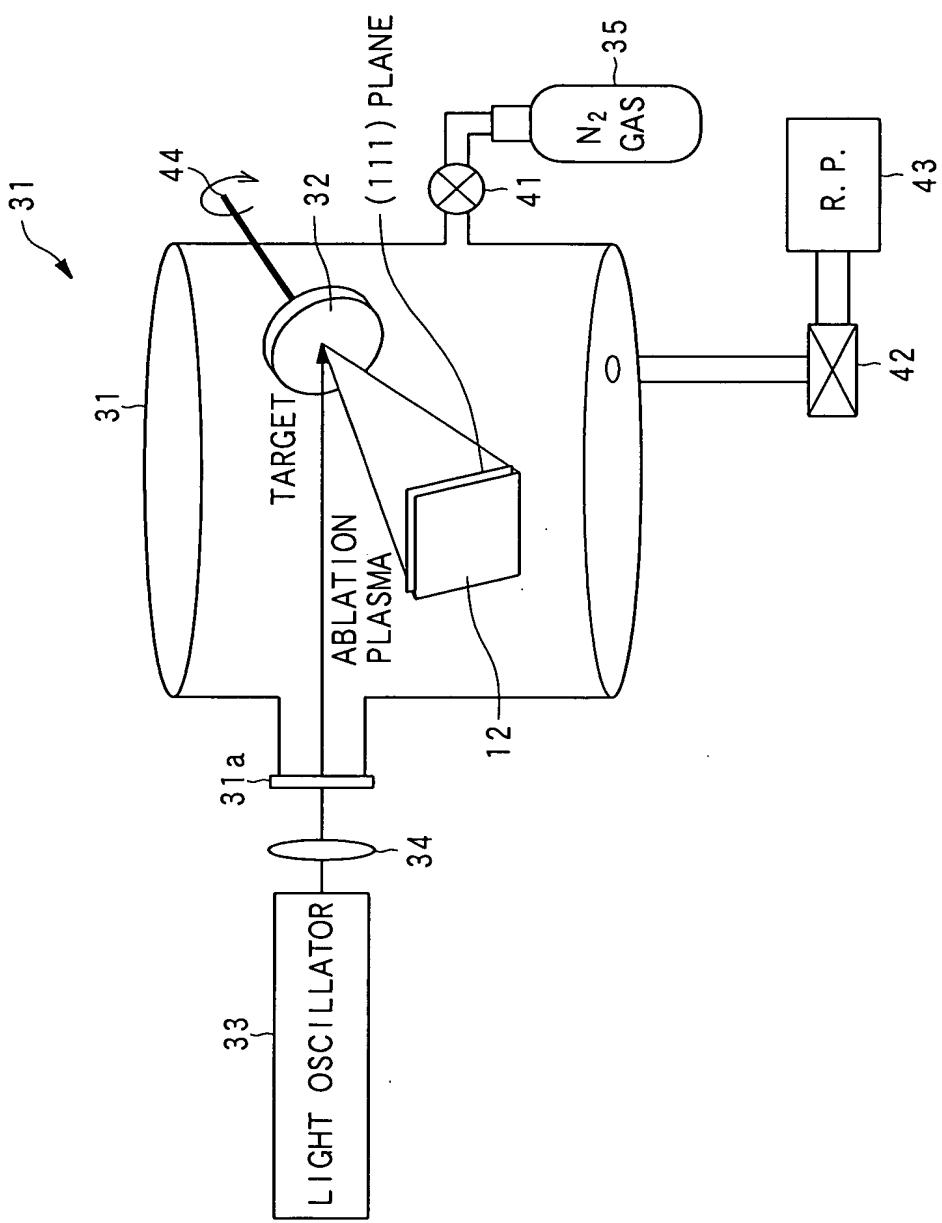
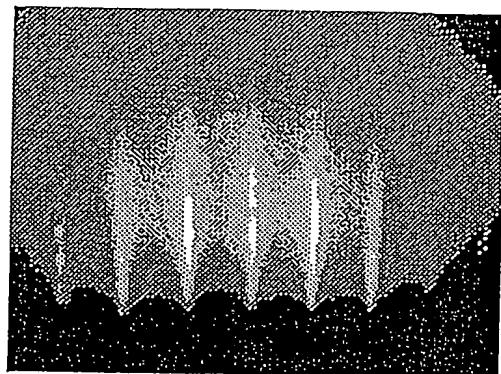


FIG. 5

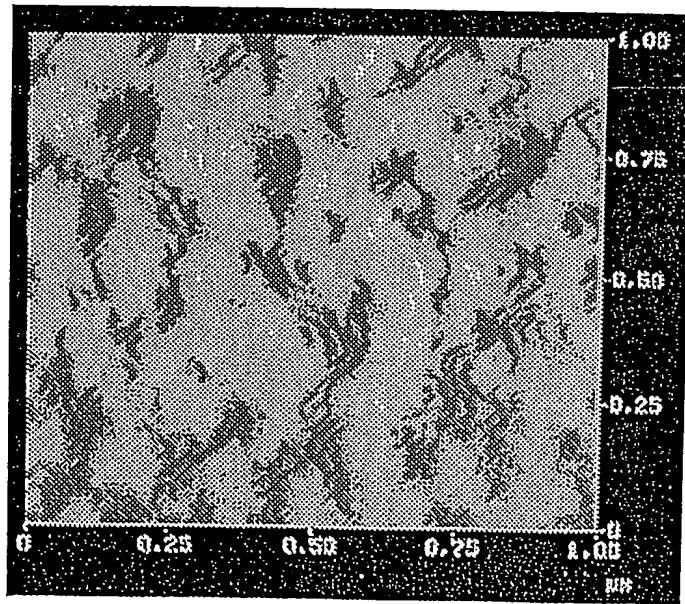
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PREPARATION THEREOF  
Filed January 6, 2006; Atty. Docket No. 113184-114

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F I G. 6



F I G. 7

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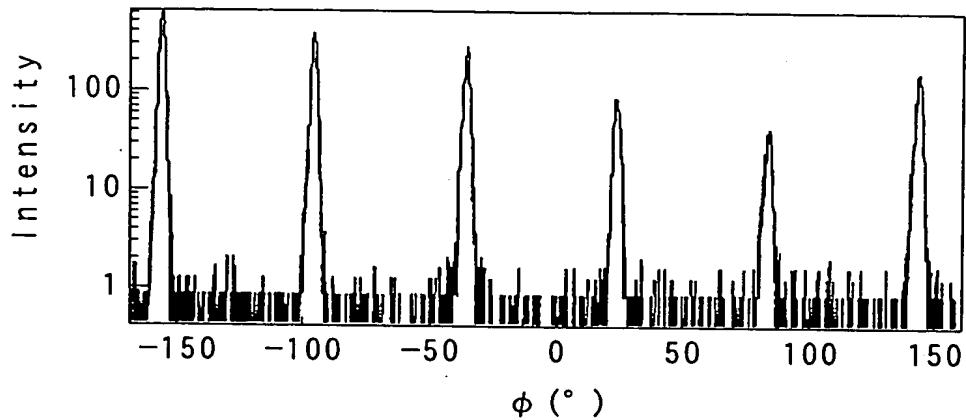


FIG. 8A

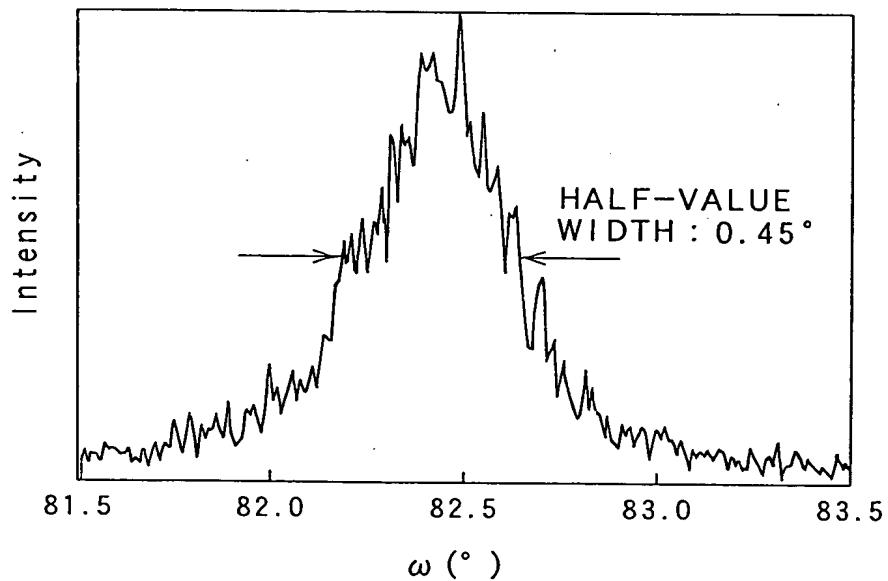


FIG. 8B

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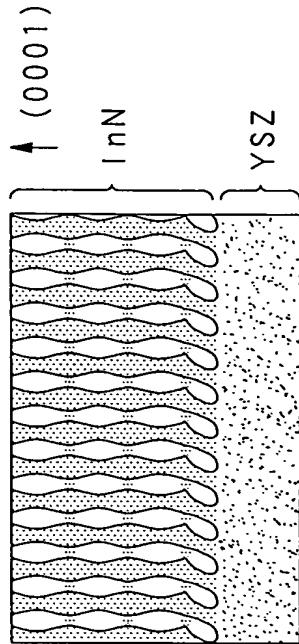


FIG. 9B

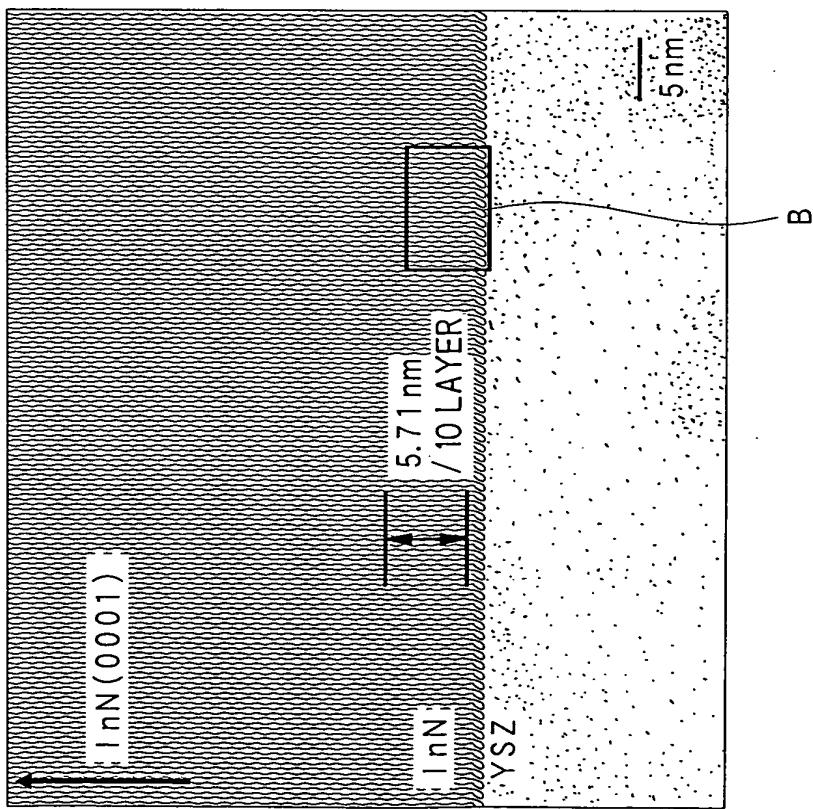


FIG. 9A

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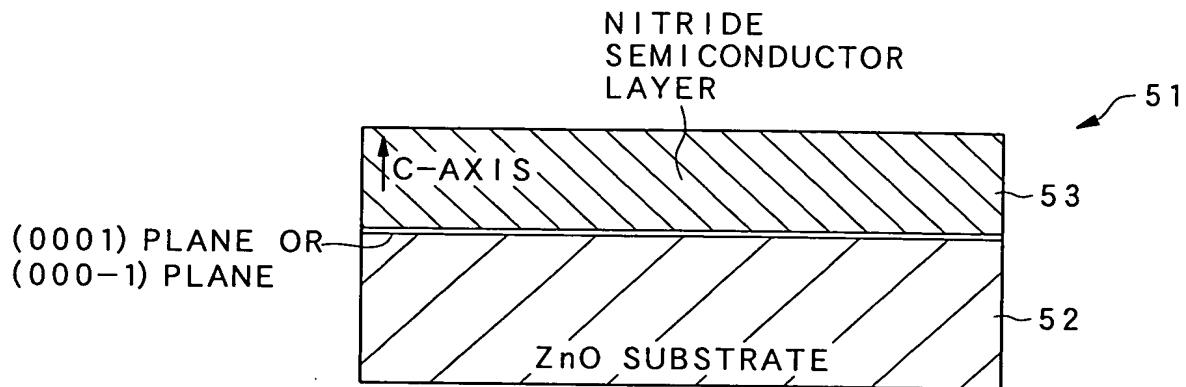


FIG.10

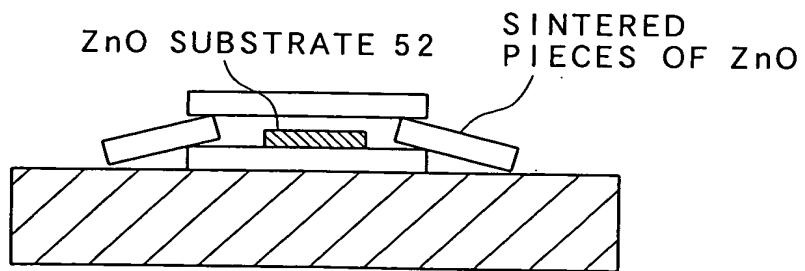
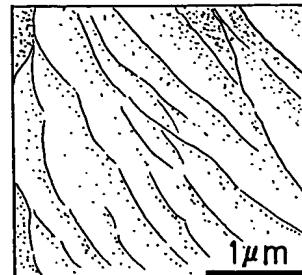


FIG.11

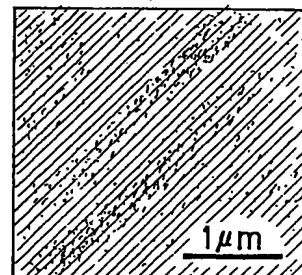
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FIG.12A



1150 °C 6.5h

FIG.12B



1150 °C 3.5h

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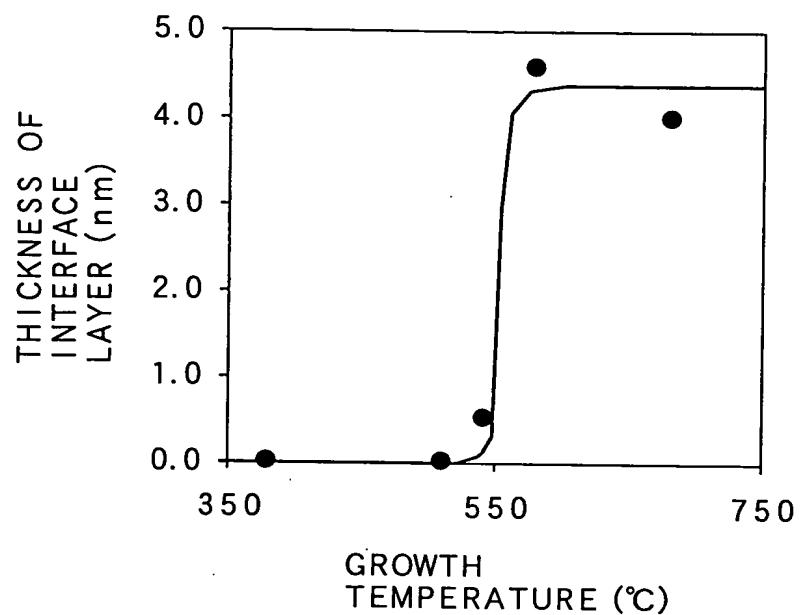


FIG. 13

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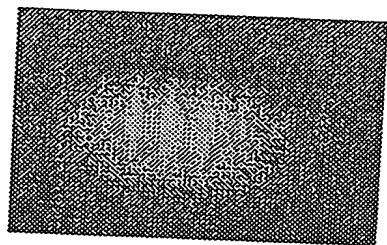


FIG. 14 A

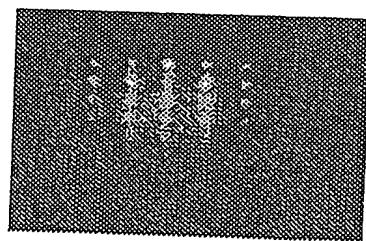


FIG. 14 B

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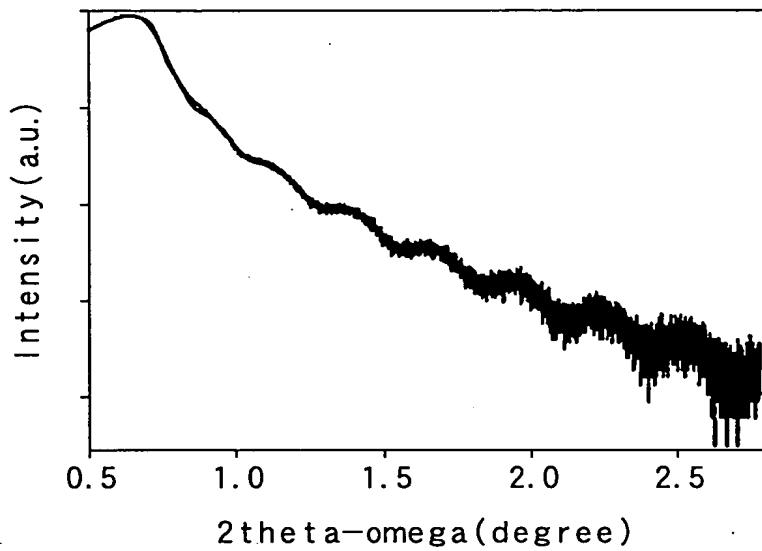
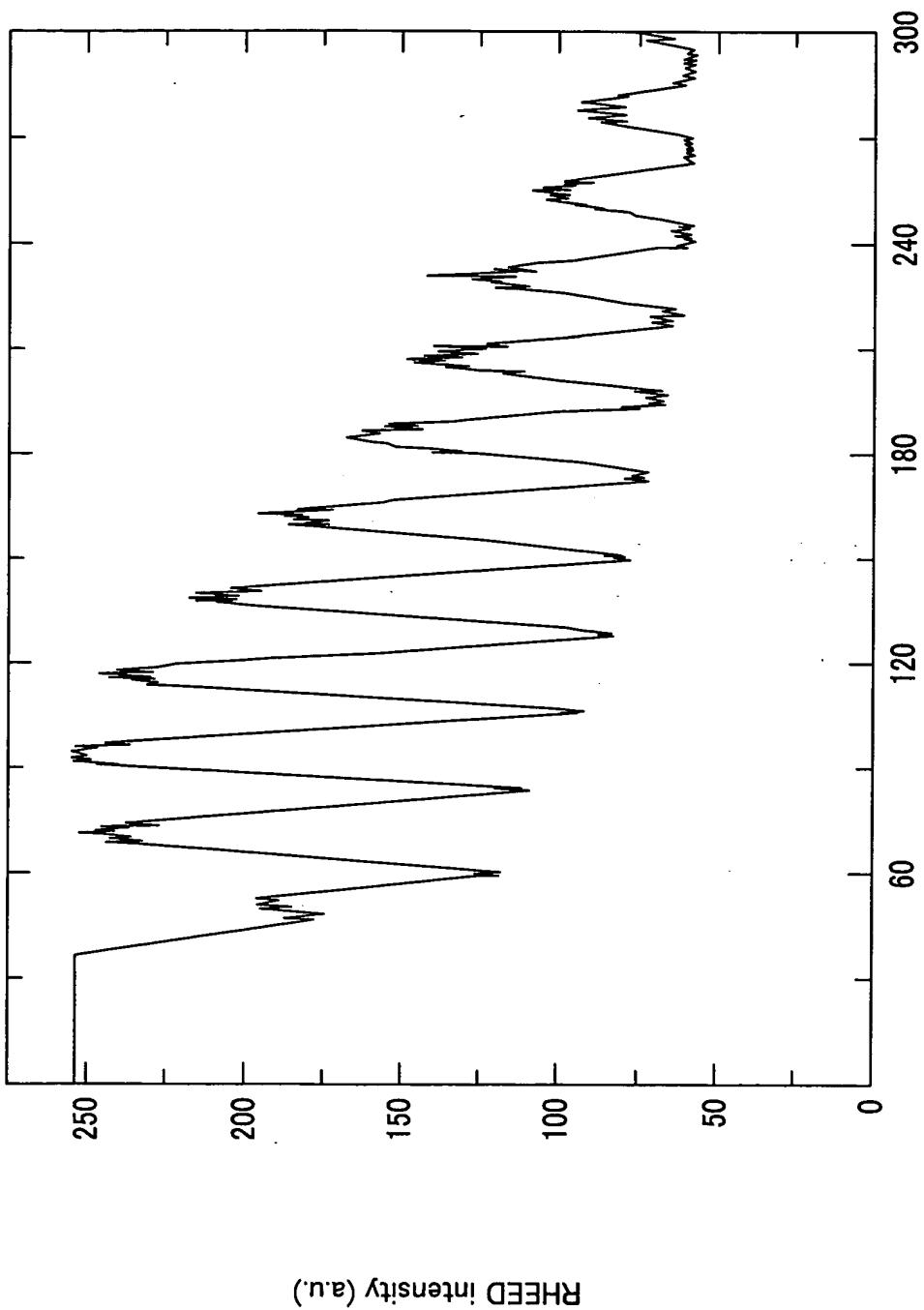


FIG.15



**FIG. 16**